

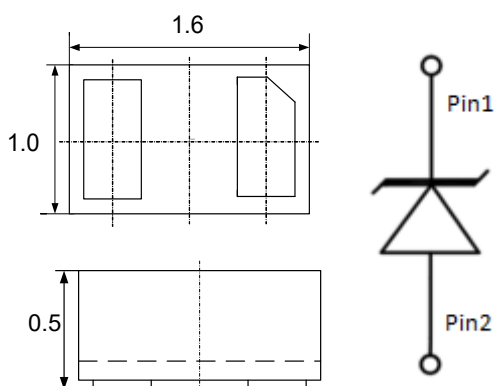
Features

- ◆ Ultra small package: 1.6x1.0x0.5mm
- ◆ Protects one data or power line
- ◆ Ultra low leakage: nA level
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
- ◆ IEC 61000-4-2 (ESD) immunity test
- ◆ Air discharge: $\pm 30\text{kV}$
- ◆ Contact discharge: $\pm 30\text{kV}$
- ◆ IEC61000-4-5 (Lightning) 110A (8/20 μs)
- ◆ RoHS Compliant
- ◆ Package: DFN1610-2

Description

The ESDJ7U0G0D6 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The ESDJ7U0G0D6 complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra- small 1.6 x1.0 x0.5 mm lead - free DFN package. The small size and high ESD surge protection make ESDJ7U0G0D6 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Circuit Diagram



Applications

- ◆ Mobile Phones
- ◆ Battery Protection
- ◆ Power Line Protection
- ◆ Vbat pin for Mobile Devices
- ◆ Hand Held Portable Applications

Absolute Maximum Ratings : ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

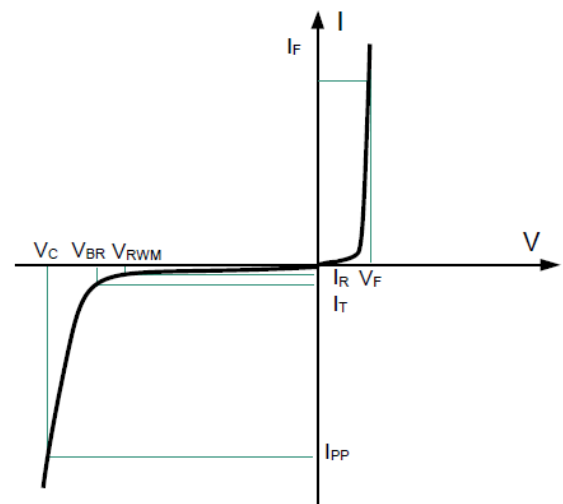
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	2200	W
Peak Pulse Current (8/20 μs)	IPP	110	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics : ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

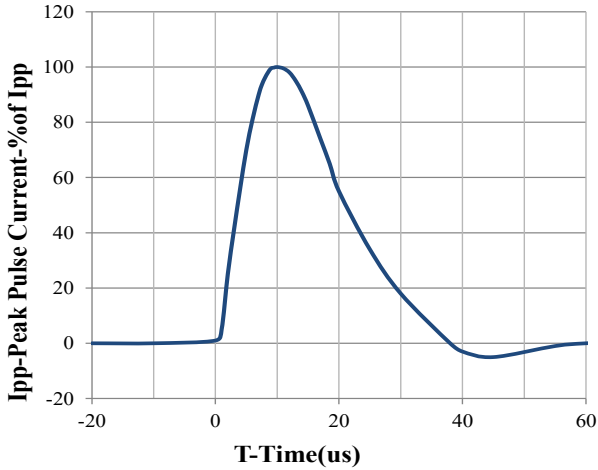
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				7	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	7.9	8.2	9.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 7\text{V}$		1	100	nA
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ (8 / 20 μs pulse)			8.3	V
Clamping Voltage	V_C	$I_{PP} = 110\text{A}$ (8 / 20 μs pulse)		13.5	20.0	V
Junction Capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$		720	1000	pF

Portion Electronics Parameter

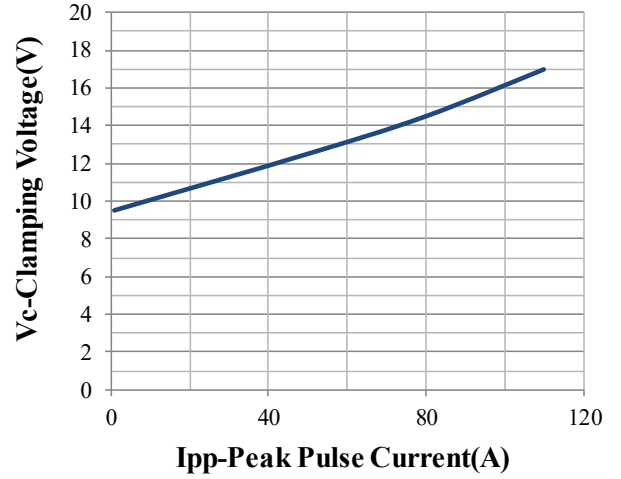
Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_F	Forward Voltage @ I_F



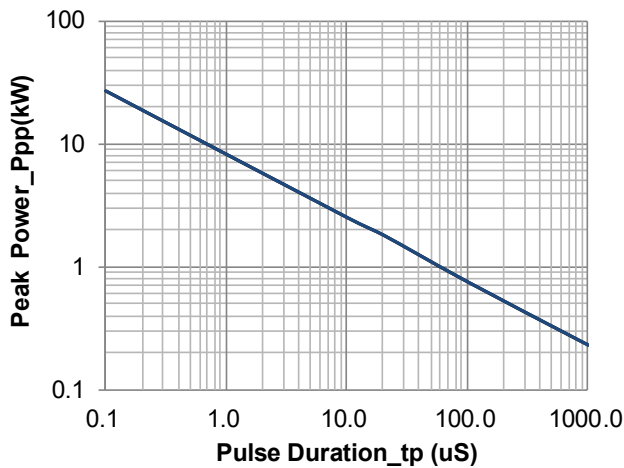
Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)



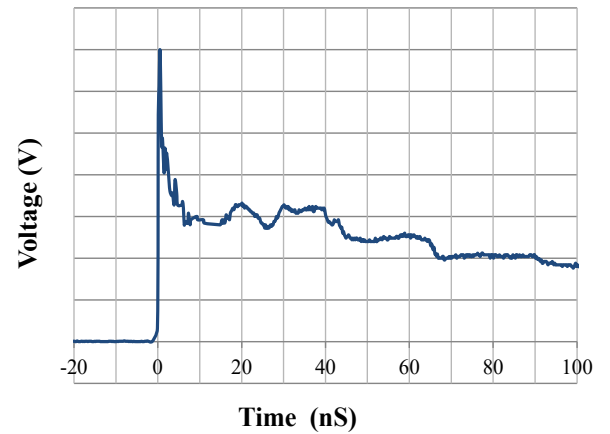
8 / 20us Pulse Waveform



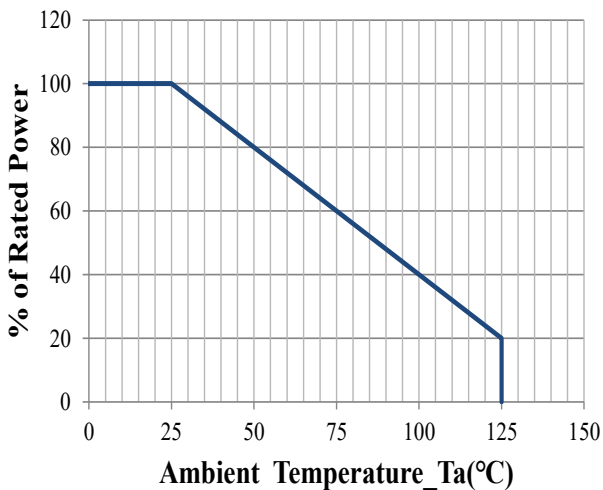
Clamping Voltage vs. Peak Pulse Current



Peak Pulse Power vs. Pulse Time



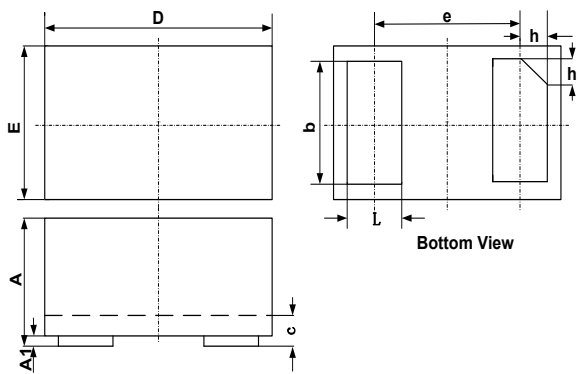
IEC61000-4-2 Pulse Waveform



Power Derating Curve

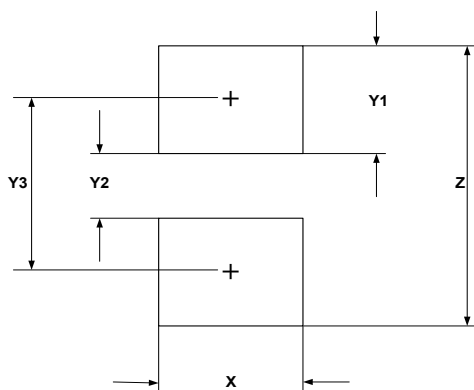
Package Dimension

DFN1610-2 Package Outline



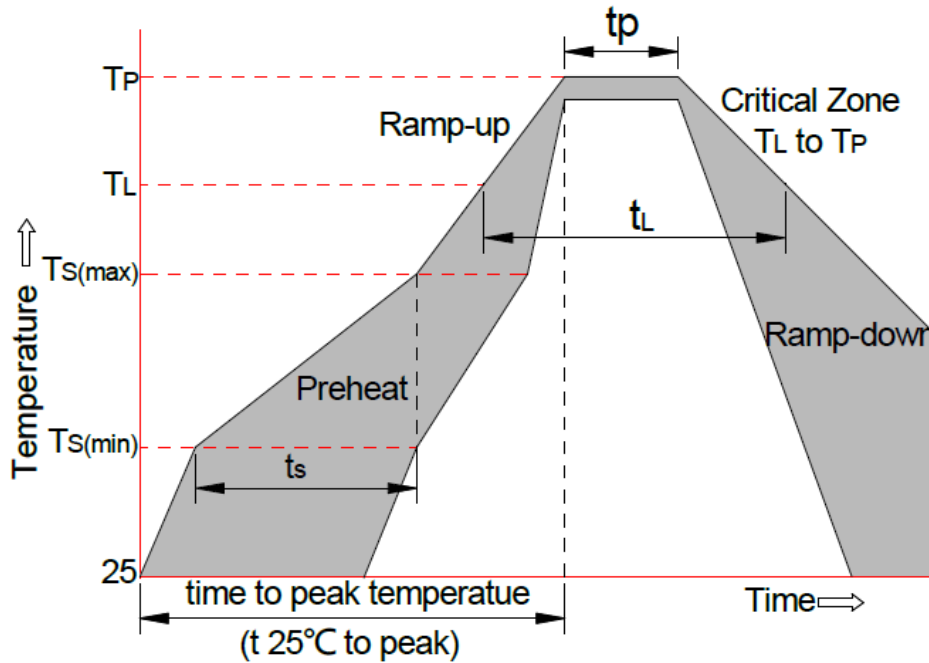
SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.75	0.80	0.85	0.030	0.032	0.034
c	0.10	0.15	0.20	0.004	0.006	0.008
D	1.55	1.60	1.65	0.062	0.064	0.066
e	1.10 BSC			0.044 BSC		
E	0.95	1.00	1.05	0.038	0.040	0.042
L	0.35	0.40	0.45	0.014	0.016	0.018
h	0.15	0.20	0.25	0.006	0.008	0.010

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	1.00	0.040
Y1	0.62	0.025
Y2	0.60	0.024
Y3	1.22	0.049
Z	1.85	0.074

Soldering Parameters



Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min (Ts (min))	+150°C
	-Temperature Max (Ts (max))	+200°C
	-Time (Min to Max) (ts)	60-180 secs
Average ramp up rate(Liquid us Temp (TL) to peak)		3°C/sec. Max
Ts (max) to TL-Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature (TL) (Liquid us)	+217°C
	-Temperature (tl)	60-150 secs
Peak Temp (Tp)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (tp)		30 secs. Max
Ramp-down Rate		6 °C/secs. Max
xTime 25°C to Peak Temp (Tp)		8 min. Max
Do not exceed		+260°C